October 1996



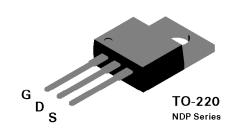
NDP5060L / NDB5060L N-Channel Logic Level Enhancement Mode Field Effect Transistor

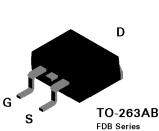
General Description

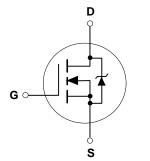
These logic level N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as automotive, DC/DC converters, PWM motor controls, and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

- $\label{eq:alpha} \begin{array}{l} \bullet \quad 26 \text{ A, } 60 \text{ V. } \text{R}_{_{\text{DS(ON)}}} = 0.05 \ \Omega \ @ \ \text{V}_{_{\text{GS}}} = 5 \text{ V} \\ \text{R}_{_{\text{DS(ON)}}} = 0.035 \ \Omega \ @ \ \text{V}_{_{\text{GS}}} = 10 \text{ V.} \end{array}$
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- 175°C maximum junction temperature rating.
- High density cell design for extremely low R_{DS(ON)}.
- TO-220 and TO-263 (D²PAK) package for both through hole and surface mount applications.







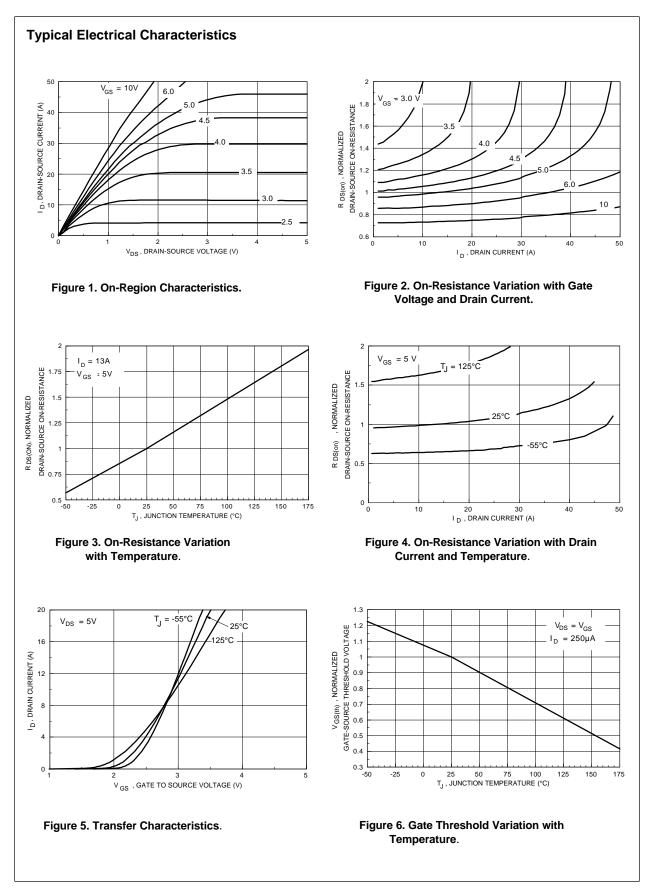
Absolute Maximum Ratings T_c = 25°C unless otherwise noted

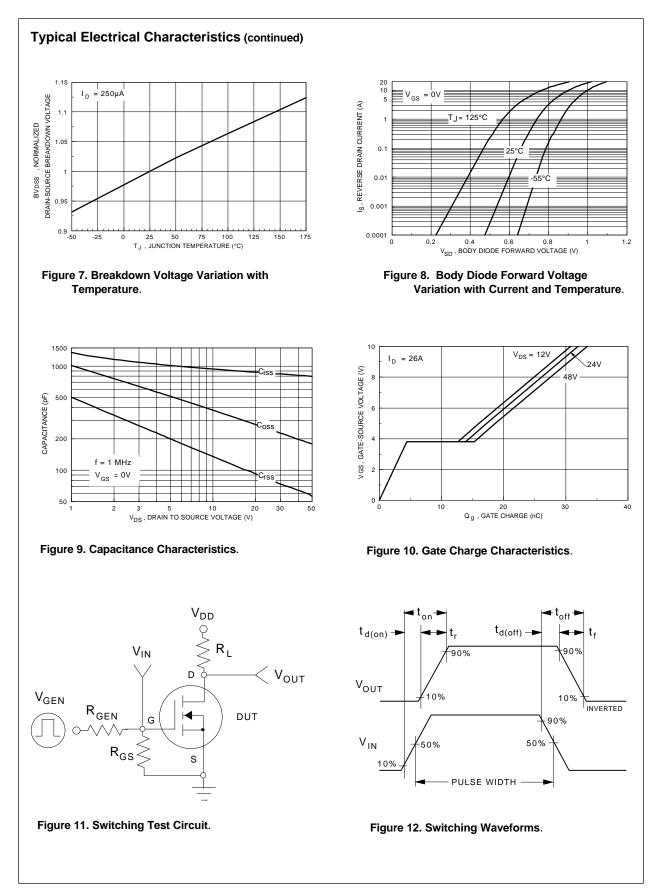
Symbol	Parameter	NDP5060L	NDB5060L	Units	
V _{DSS}	Drain-Source Voltage	60		V	
V_{DGR}	Drain-Gate Voltage ($R_{GS} \le 1 M\Omega$)	60		V	
V_{GSS}	Gate-Source Voltage - Continuous	±16		V	
	- Nonrepetitive ($t_p < 50 \ \mu s$)	±25			
I _D	Drain Current - Continuous 26		26	А	
	- Pulsed	78			
P _D	Total Power Dissipation @ $T_c = 25^{\circ}C$	6	68		
	Derate above 25°C	0.	W/°C		
TJ,TSTG	Operating and Storage Temperature Range	-65 t	o 175	°C	

Symbol	Parameter	Conditions		Min	Тур	Max	Units
DRAIN-S	OURCE AVALANCHE RATINGS (Note 1)						
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	V _{DD} = 30 V, I _D = 26 A				100	mJ
I _{AR}	Maximum Drain-Source Avalanche Curre	ent				26	А
OFF CH/	ARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$		60			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{\rm DS} = 60 \text{ V}, V_{\rm GS} = 0 \text{ V}$				250	μA
			T _J = 125°C			1	mA
I _{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 16 \text{ V}, V_{DS} = 0 \text{ V}$	·			100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -16 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$				-100	nA
ON CHA	RACTERISTICS (Note 1)						
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		1	1.4	2	V
			T _J = 125°C	0.65	1	1.5	
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 5 \text{ V}, I_{D} = 13 \text{ A}$	·		0.042	0.05	Ω
			T _J = 125°C		0.07	0.08	
		$V_{GS} = 10 \text{ V}, I_{D} = 13 \text{ A}$	·		0.031	0.035	ľ
I _{D(on)}	On-State Drain Current	$V_{GS} = 5 \text{ V}, V_{DS} = 10 \text{ V}$		26			А
9 _{FS}	Forward Transconductance	$V_{\rm DS} = 10 \text{ V}, \text{ I}_{\rm D} = 13 \text{ A}$			16		S
DYNAMI	C CHARACTERISTICS						
C _{iss}	Input Capacitance	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz			840		pF
C _{oss}	Output Capacitance				230		pF
C _{rss}	Reverse Transfer Capacitance				75		pF
SWITCHI	NG CHARACTERISTICS (Note 1)						
t _{D(on)}	Turn - On Delay Time	$V_{DD} = 30 \text{ V}, \ I_{D} = 26 \text{ A}, \\V_{GS} = 5 \text{ V}, \ R_{GEN} = 30 \Omega \\R_{GS} = 30 \Omega$			13	20	nS
t,	Turn - On Rise Time				200	400	nS
t _{D(off)}	Turn - Off Delay Time				45	80	nS
t _f	Turn - Off Fall Time				102	200	nS
Q _g	Total Gate Charge	$V_{DS} = 24 V,$ $I_{D} = 26 A, V_{GS} = 5 V$			17	24	nC
Q _{gs}	Gate-Source Charge				4		nC
Q _{gd}	Gate-Drain Charge				10		nC

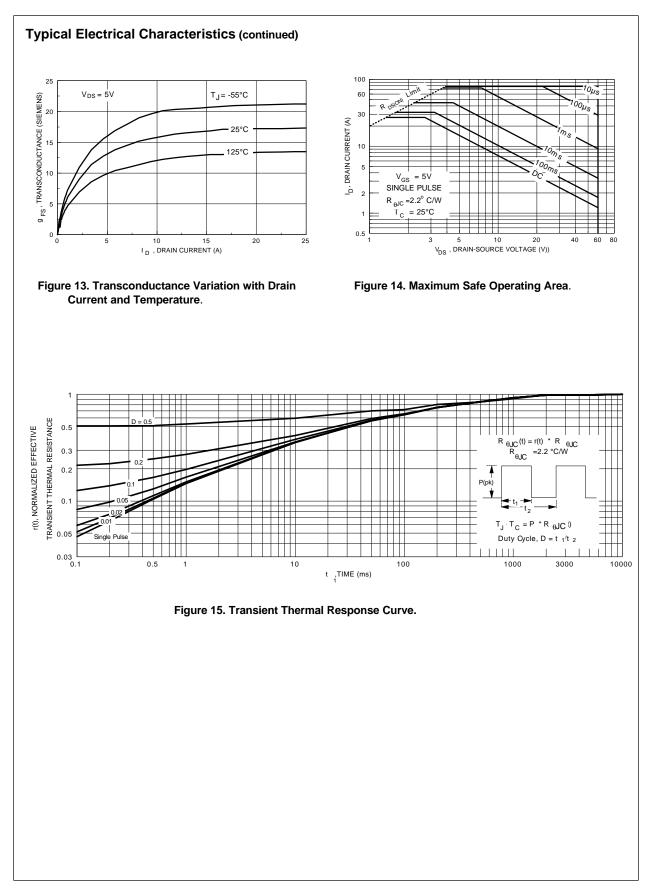
Electrical Characteristics (T _c = 25°C unless otherwise noted)						
Symbol	Parameter	Conditions	Min	Тур	Max	Units
DRAIN-S	OURCE DIODE CHARACTERISTICS		•			
I _s	Maximum Continuos Drain-Source Diode Forward Current				26	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				78	А
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{S} = 13 \text{ A} \text{ (Note 1)}$		0.9	1.3	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 V, I_F = 26 A,$ $dI_F/dt = 100 A/\mu s$		54	120	ns
l _m	Reverse Recovery Current			2.1	8	Α
THERMA	L CHARACTERISTICS	· ·	÷		•	
R _{θJC}	Thermal Resistance, Junction-to-Case				2.2	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient				62.5	°C/W

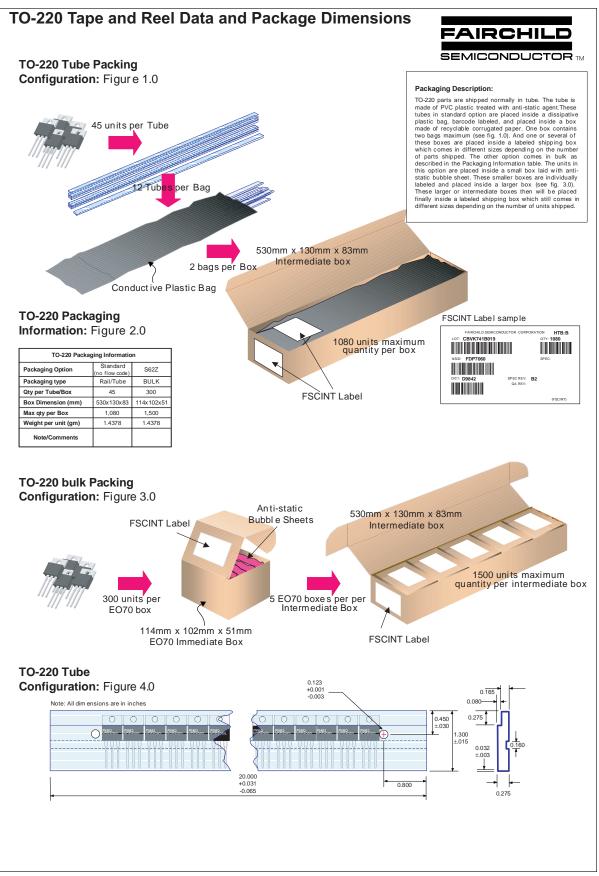
Note: 1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.



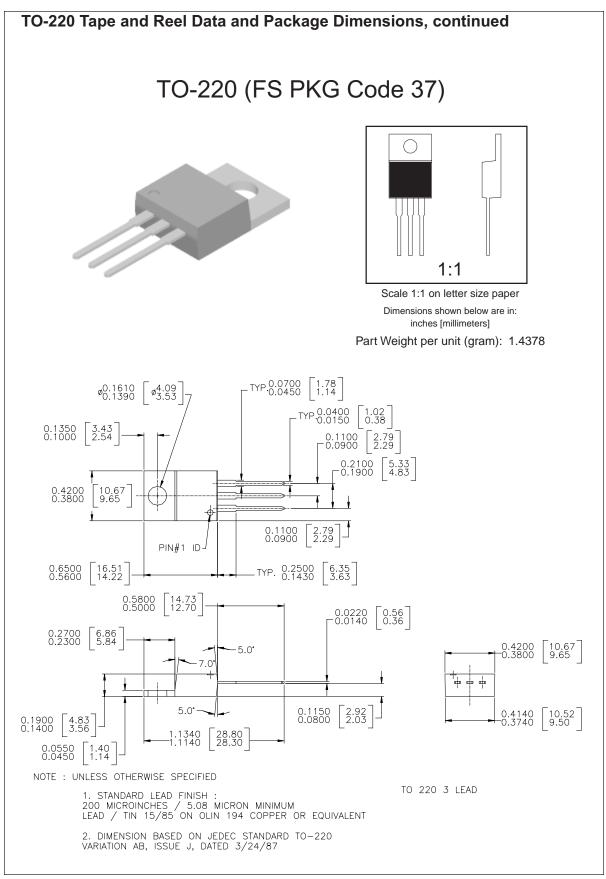


NDP5060L Rev.A

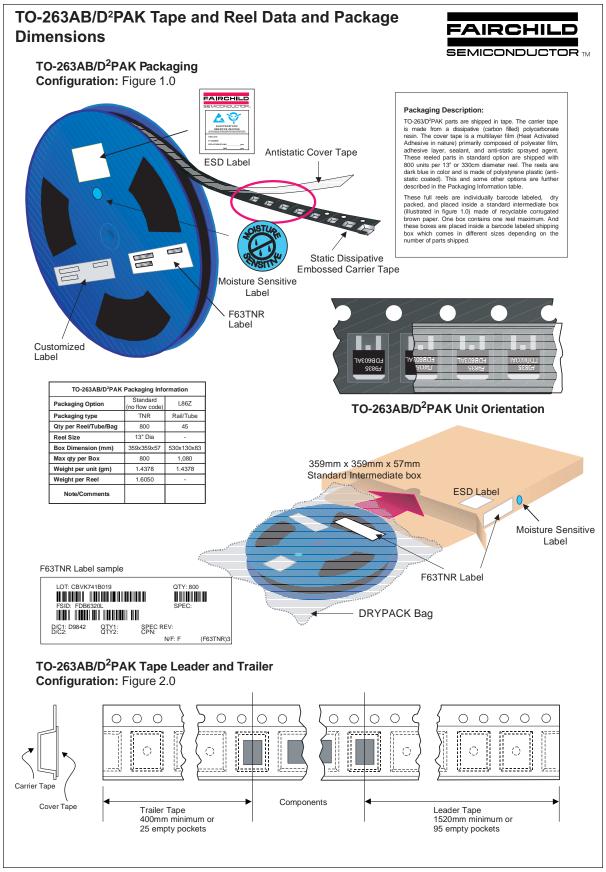




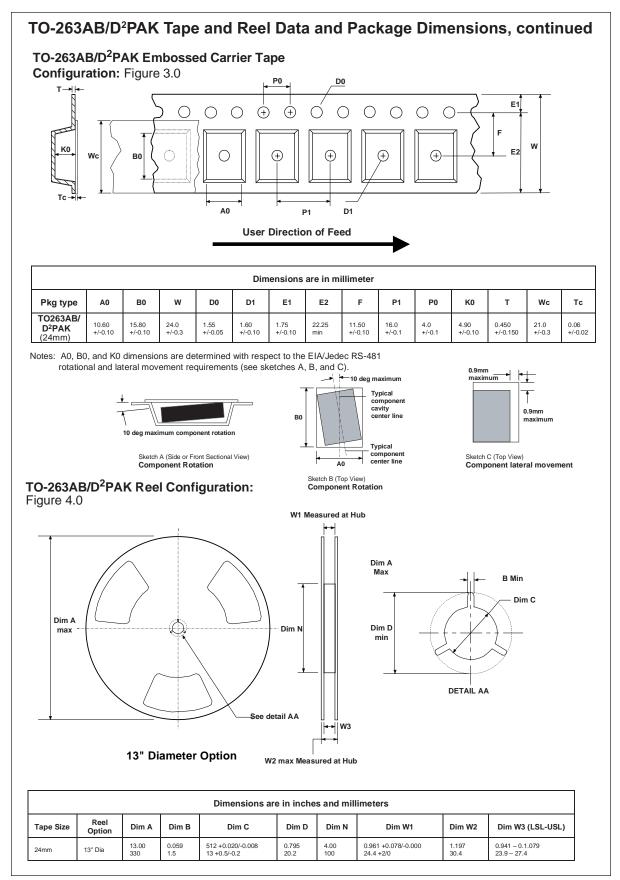
August 1999, Rev. B

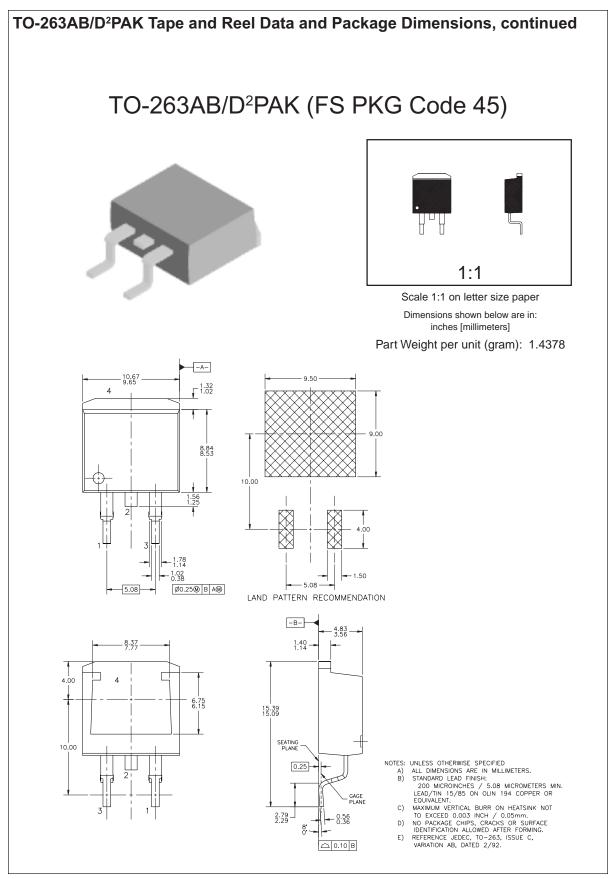


September 1998, Rev. A



September 1999, Rev. B





August 1998, Rev. A

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACExTM CoolFETTM CROSSVOLTTM E²CMOSTM FACTTM FACT Quiet SeriesTM FAST[®] FAST[®] FASTrTM GTOTM HiSeCTM ISOPLANAR™ MICROWIRE™ POP™ PowerTrench® QFET™ QS™ Quiet Series™ SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SyncFET™ TinyLogic™ UHC™ VCX™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user. 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.



Authorized Distribution Brand :



Website :

Welcome to visit www.ameya360.com

Contact Us :

➤ Address :

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd Minhang District, Shanghai , China

- > Sales :
 - Direct +86 (21) 6401-6692
 - Email amall@ameya360.com
 - QQ 800077892
 - Skype ameyasales1 ameyasales2

> Customer Service :

Email service@ameya360.com

> Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com